

AMENDMENTS TO THE CLAIMS

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1. (Previously presented) A semiconductor device, comprising:
a semiconductor substrate; and
a conductive layer formed on said semiconductor substrate and including polycrystals, said conductive layer including in its surface a recess caused by a crystal grain boundary and having side walls formed such that a distance therebetween becomes small as closer to said semiconductor substrate, wherein said conductive layer includes:
a first conductive layer having a substantially planar upper surface, formed on said semiconductor substrate and including a polycrystal having a first average grain size;
a second conductive layer formed on said first conductive layer, including a polycrystal having a second average grain size greater than said first average grain size and having said recess; and
said recess is formed directly over the substantially planar upper surface of the first conductive layer.

2. (Cancelled)

~~2~~ 3. (Original) The semiconductor device according to claim 1, further comprising a thin film layer formed on said conductive layer and having a material different from that of said conductive layer.

~~3~~ 4. (Original) The semiconductor device according to claim 1, wherein said conductive layer includes aluminum.

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~~4~~ 5. (Original) The semiconductor device according to claim 1, further comprising an insulating layer formed on said semiconductor substrate and a barrier layer formed on said insulating layer, said conductive layer being formed on said barrier layer.

6-20. (Cancelled)